

Computer Organization & Architecture

## 3-4 Structure of Larger Memories

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# Contents of this lecture

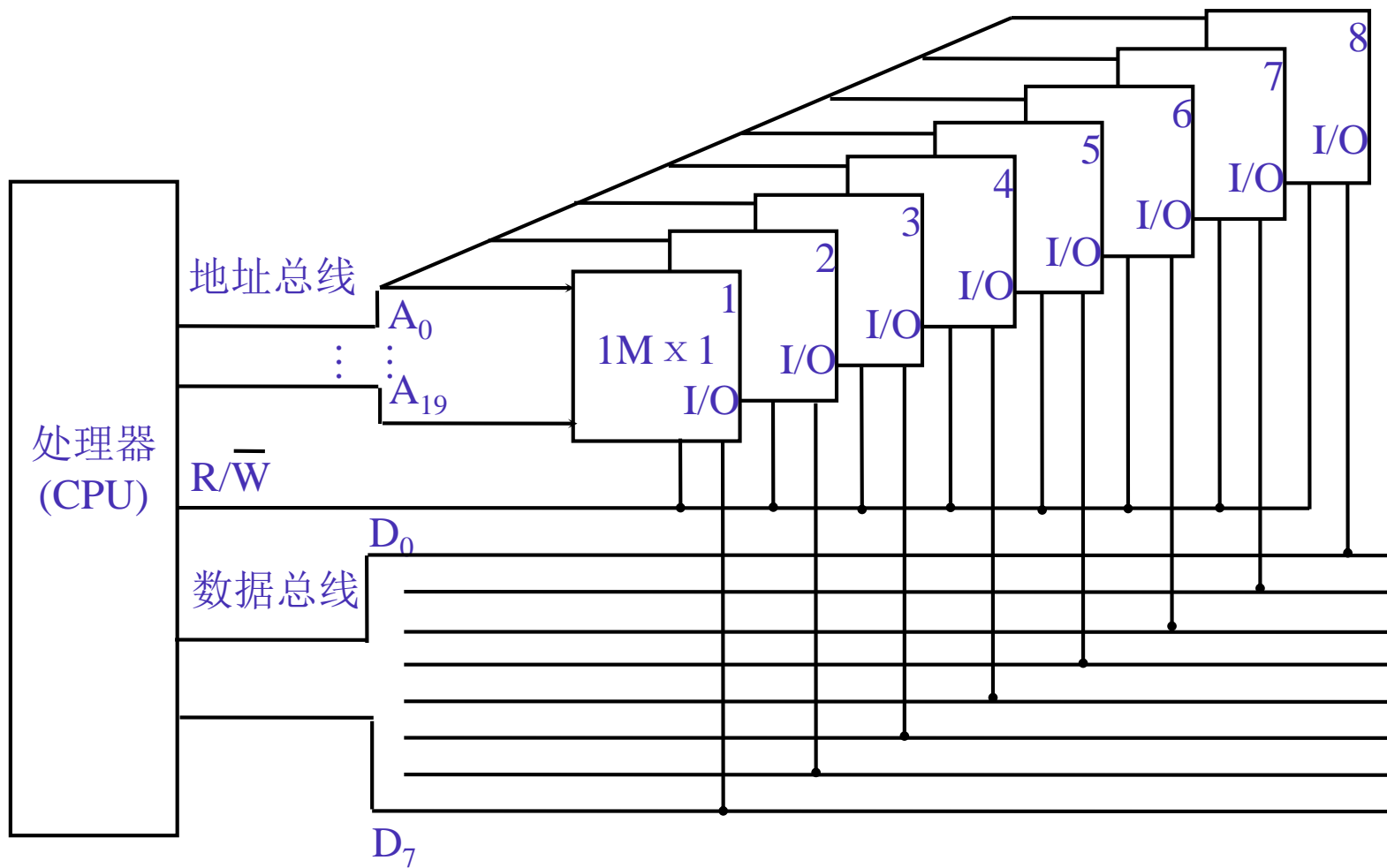
- Static Memory Systems
  - How to connect a number of static memory chips to form a much larger memory?
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# Static Memory System (1)

- 位扩展法

- 芯片每个存储单元的位数小于存储器字长，需进行位扩展
- 例：用 $1\text{M} \times 1$ 位存储芯片组成 $1\text{M} \times 8$ 位 (1MB)的存储器
  - 共需8片 $1\text{M} \times 1$ 位的芯片，每片存储同一位权的一位数据(片的I/O端接 $D_i$ )
  - 访问芯片需20位地址码 $A_{19} \sim A_0$
  - 读写控制信号 $R/\overline{W}$

# Static Memory System (2)

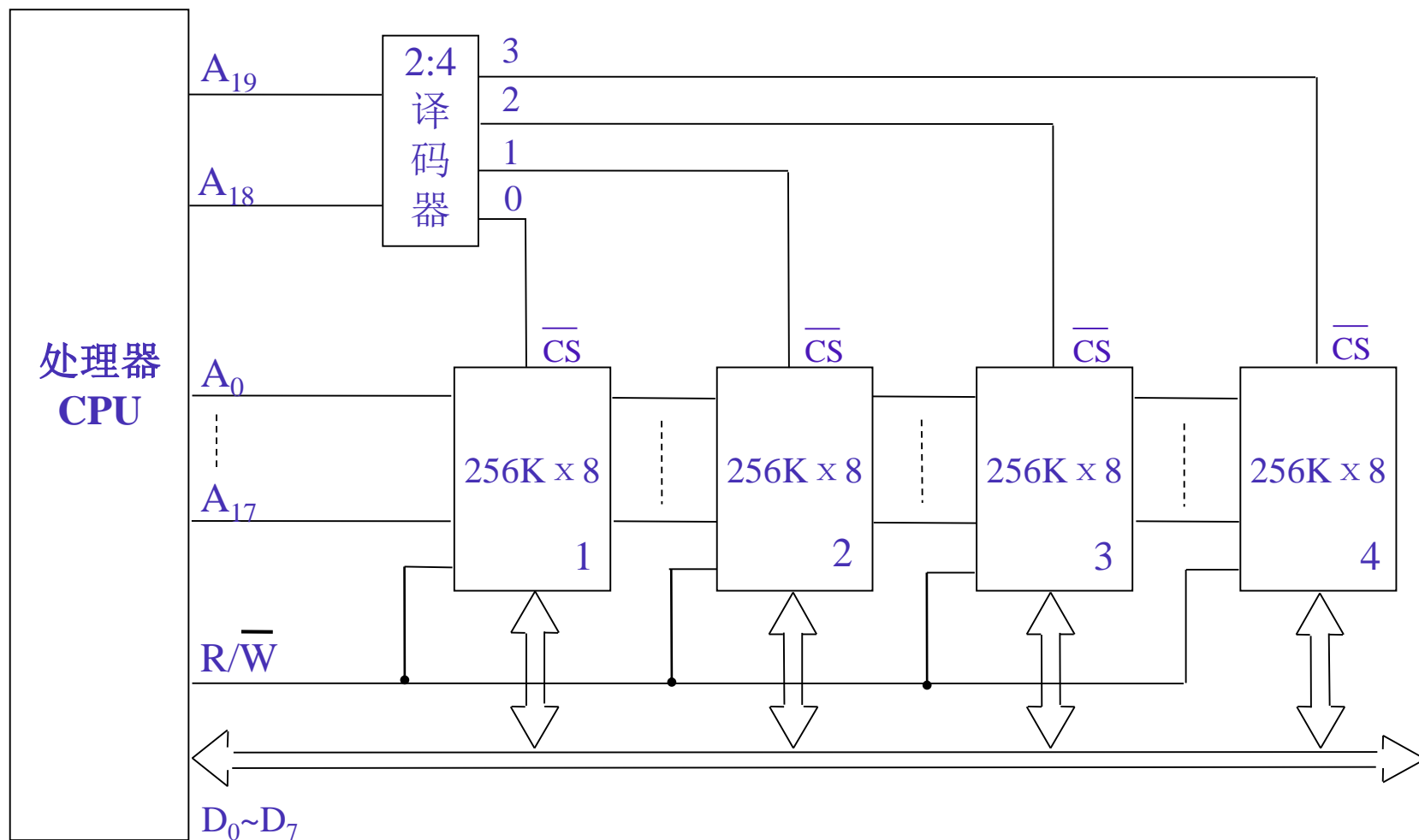


# Static Memory System (3)

- 字扩展法

- 芯片每个存储单元的位数等于存储器字长，但容量(字数)不够，需进行字扩展
- 例：用 $256\text{K} \times 8$ 位芯片组成 $1\text{M} \times 8$ 的存储器
  - 共需 $1\text{M}/256\text{K}=4$ 片 $256\text{K} \times 8$ 位的芯片
  - $1\text{MB}$ 容量需20位地址码( $A_{19} \sim A_0$ )，而 $256\text{KB}$ 芯片需18位片内地址码( $A_{17} \sim A_0$ )
  - 用高二位地址 $A_{19}A_{18}$ 经2:4译码器选择芯片读/写
  - 每片8条I/O线分别接 $D_7 \sim D_0$

# Static Memory System (4)

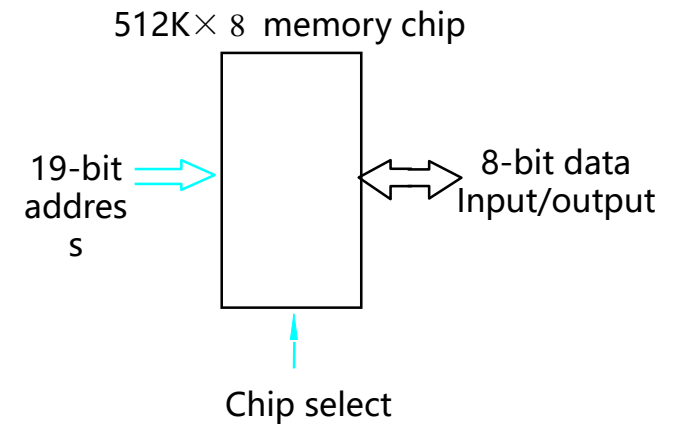
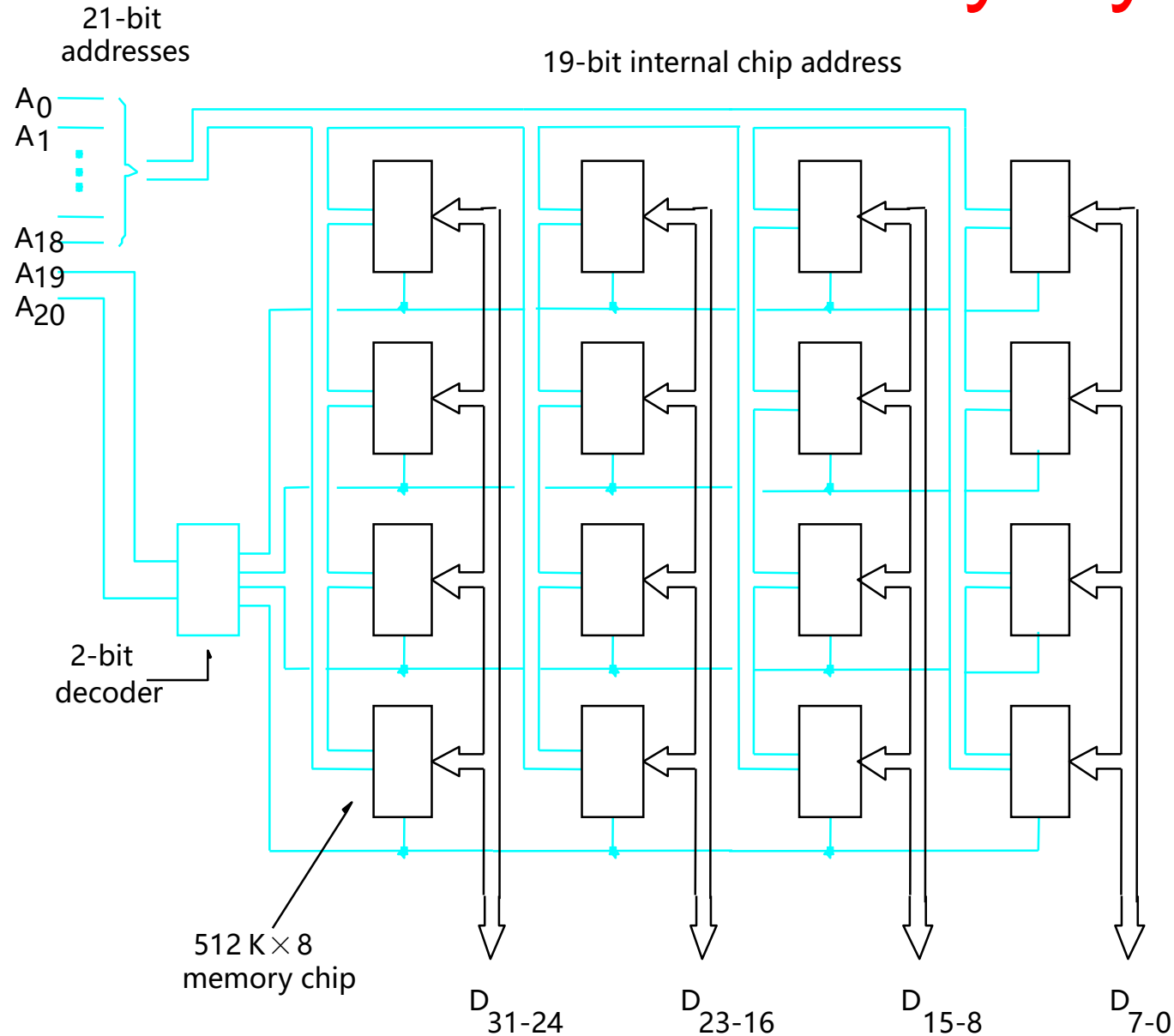


# Static Memory System (5)

- 字位同时扩展法

- 单片芯片的字数和位数均小于主存的容量要求，需进行字、位的扩展
- 例：用**512K×8**位的存储器芯片组成**2M×32**位的存储器
  - 共需  $\frac{2 \times 1024}{512} \times \frac{32}{8} = 4 \times 4 = 16$  片**512K×8**位的芯片，组成**4×4**的阵列
  - **2M×32**容量需**21**位地址码( $A_{20} \sim A_0$ )，而**512KB**芯片需**19**位片内地址码( $A_{18} \sim A_0$ )
  - 用高二位地址 **$A_{20}A_{19}$** 经**2:4**译码器选择一行芯片读/写
  - 每片**8**条**I/O**线分别接 **$D_7 \sim D_0$**

# Static Memory System (6)





# Static Memory System (7)

- Conclusion
  - Assume that the capacity of a memory unit is  $M \times N$  bit, if constituted of using  $I \times k$  bit chips, the number of total chips needed is  $(M/I) \times (N/k)$ .

# Dynamic Memory System (1)

- The organization of large dynamic memory systems is essentially the same as the above static memory system
- Packaging: Memory Modules
  - Memory module: Assembly memory chips on a small board that plugs into a socket on the computer's motherboard
    - SIMM (Single In-line Memory Modules)
    - DIMM (Dual In-line Memory Modules)

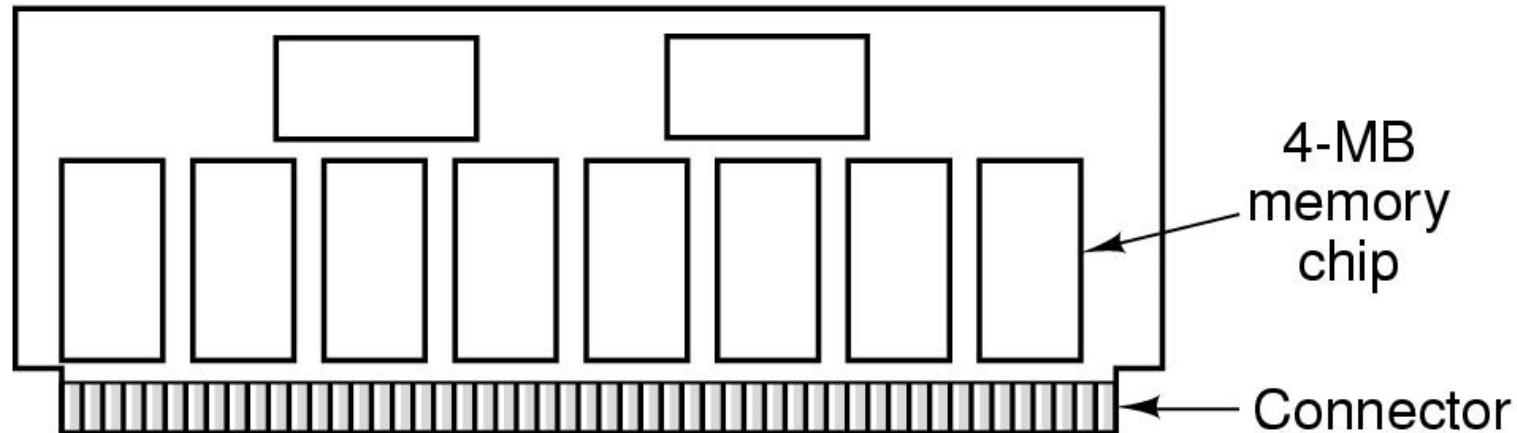
# Dynamic Memory System (2)

- SIMM
  - A SIMM is a basic DRAM packaging type that fits most older systems.
  - A SIMM can be either single-sided (with RAM chips on one side only) or double-sided (with RAM chips on both sides).
    - 30-pin SIMM: 1-16MB; 8 bits; plus 1bit for parity; single-sided
    - 72-pin SIMM: 1MB, 4MB, 16MB (single-sided); 2MB, 8MB, 32MB (double-sided); 32 bits, plus 4 bits for parity/ECC

# Dynamic Memory System (3)

- SIMM Example

- A single inline memory module (SIMM) holding 32MB. Two of the chips control the SIMM



# Dynamic Memory System (4)

- DIMM
  - At present, DIMMs are the standard way for memory to be packaged.
  - A DIMM is capable of delivering 64 data bits at once.
  - Most common types of DIMMs
    - 72-pin, 144-pin, 200-pin DIMMs: used for SO-DIMM (Small Outline DIMM)
    - 168-pin DIMMs, used for FPM (Fast Page Mode) DRAM, EDO (Extended Data Out) DRAM, and SDRAM
    - 184-pin DIMMs, used for DDR SDRAM
    - 240-pin DIMMs, used for DDR2 and DDR3 SDRAM
    - 284-pin DIMMs, used for DDR4 SDRAM
    - 288-pin DIMMs, used for DDR5 SDRAM

# Dynamic Memory System (5)

- DIMM Example
  - Two types of DIMMs: a 168-pin SDRAM module (top) and a 184-pin DDR SDRAM module (bottom)



# Example

- CPU的地址总线16根 (A15~A0, A0为低位), 双向数据总线8根 (D7 ~ D0), 控制总线中与主存有关的信号有 $\overline{\text{MREQ}}$  (允许访存, 低电平有效),  $\text{R}/\overline{\text{W}}$  (高电平为读命令, 低电平为写命令)
- 主存地址空间分配如下:  $0000_{\text{H}} \sim 3\text{FFF}_{\text{H}}$  为系统程序区, 由只读存储芯片组成;  $4000_{\text{H}} \sim 4\text{FFF}_{\text{H}}$  为系统程序工作区, 由SRAM组成;  $6000_{\text{H}} \sim 9\text{FFF}_{\text{H}}$  为用户程序区, 也由SRAM组成。  
按字节编址。现有如下存储器芯片:
  - EPROM:  $8\text{K} \times 8$ 位 (控制端仅有 CS)
  - SRAM:  $16\text{K} \times 1$ 位,  $2\text{K} \times 8$ 位,  $4\text{K} \times 8$ 位,  $8\text{K} \times 8$ 位
- 请从上述芯片中选择适当芯片设计该计算机主存储器, 画出主存储器逻辑框图, 注意画出选片逻辑 (可选用门电路及3:8译码器74LS138) 与CPU的连接, 说明选哪些存储器芯片及选多少片。

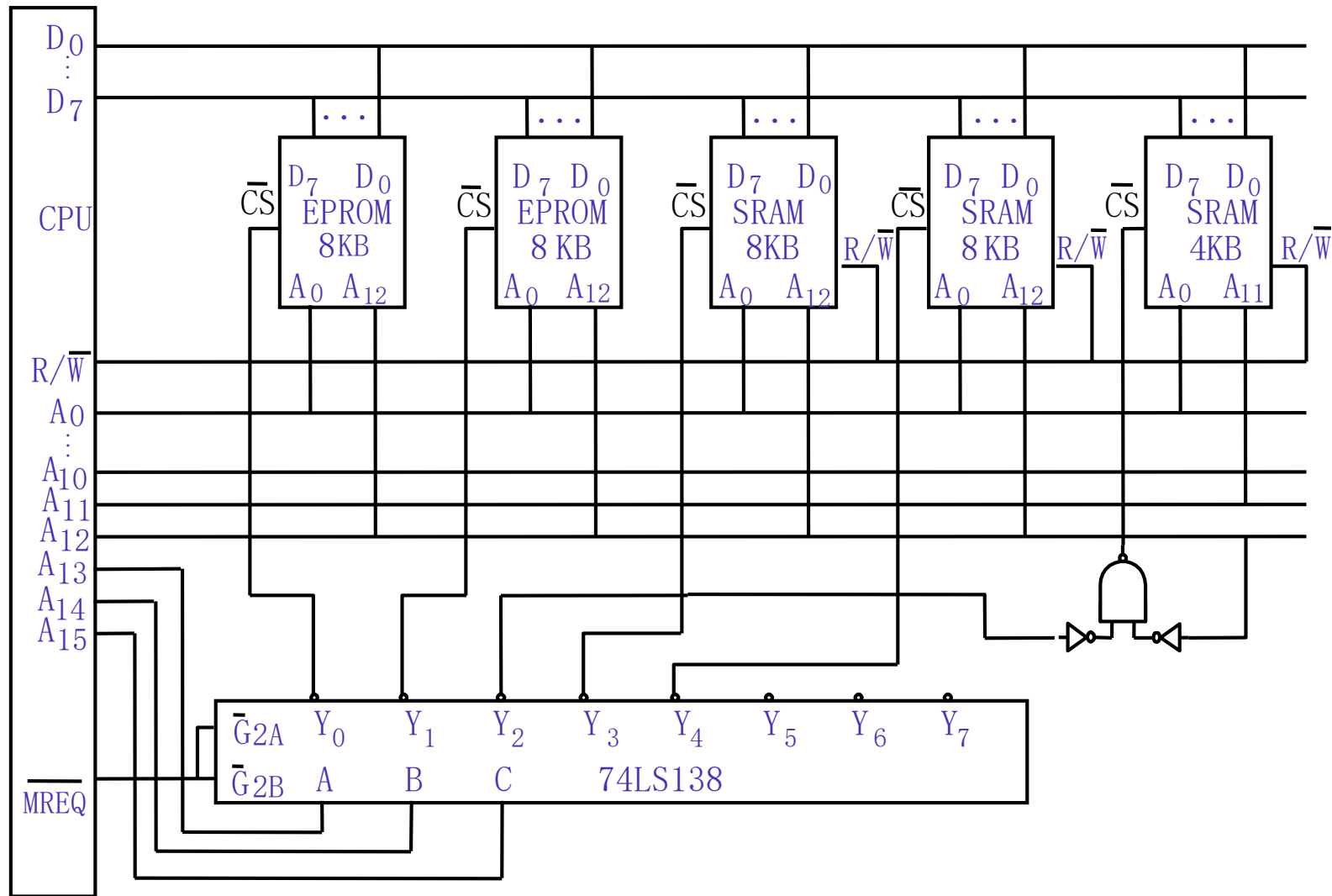
# Example (ctd.)

- 主存地址空间分布:

{ 0000 <sub>H</sub> 3FFF <sub>H</sub>	16KB(EPROM)
{ 4000 <sub>H</sub> 4FFF <sub>H</sub>	4KB(SRAM)
	4KB(空)
{ 6000 <sub>H</sub> 9FFF <sub>H</sub>	16KB(SRAM)
{ A000 <sub>H</sub> FFFF <sub>H</sub>	24KB(空)



# Example (ctd.)



# Quiz (1)

1. Consider a  $16\text{M} \times 128$  memory built by using  $512\text{K} \times 16$  memory chips. How many rows of memory chips are needed?

A. 8                      B. 16                      C. 32                      D. 64

$$16\text{M}/512\text{K}=32$$

2. Consider a  $64\text{M} \times 16$  memory built by using  $512\text{K} \times 8$  memory chips. How many memory chips are needed?

A. 32                      B. 64                      C. 128                      D. 256

$$(64\text{M} \times 16)/(512\text{K} \times 8)=256$$

## Quiz (2)

3. Consider a memory can be accessed with 20-bit address. Its word length is 64-bit and it is word-addressable. Assume that we use  $256\text{K} \times 8\text{bit}$  SRAM chip to constitute this memory.

- How many bytes can this memory store?

$$2^{20} * 64 / 8 \text{ B} = 1\text{M} * 8 \text{ B} = 8 \text{ MB}$$

- How many SRAM chips do we need?

$$8\text{MB} / (256\text{K} * 8 / 8 \text{ B}) = 8\text{MB} / 256\text{KB} = 32\text{片}$$

- How many address pins do we need for chip select? Why?

因为每片芯片内部有18位地址 (对应于256K个存储单元)，所以，20位的地址中，低18位地址直接接芯片的18位地址端，高2位地址通过2:4译码器作芯片选择。

- Draw a figure to show how this memory can be implemented using  $256\text{K} \times 8\text{bit}$  SRAM chip.

## Quiz (3)

4. Assume that there are two types of static memory chips:  $128K \times 8$  bit (total 4 chips) and  $512K \times 4$  bit (total 2 chips). Please use these memory chips to implement a  $512K \times 16$  bit memory. Draw the figure of the memory organization.

# Solution

512K×16的存储器需要2片512K×4 和4片128K×8的芯片按下图组成。

